



NCE P-Channel Enhancement Mode Power MOSFET

Description

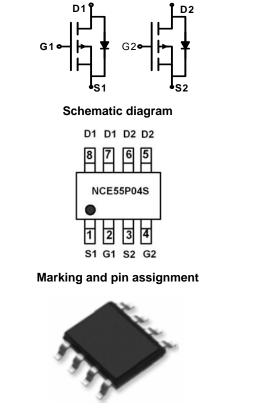
The NCE55P04S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} =-55V,I_D =-4A
 R_{DS(ON)} <82mΩ @ V_{GS}=-10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- DC-DC Converter



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE55P04S	NCE55P04S	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25[°]Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	-55	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	-4	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	-2.8	А
Pulsed Drain Current	I _{DM}	-25	А
Maximum Power Dissipation	P _D	3	W
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 150	°C

Thermal Characteristic

Thermal Resistance ,Junction-to-Ambient ^(Note 2)	R _{θJA}	42	°C/W
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Electrical Characteristics (T_A=25[°]C unless otherwise noted)







Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-55	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-55V, V_{GS} =0V	-	-	-1	μA	
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1.5	-2.6	-3.5	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =-10V, I _D =-4A	-	66	82	mΩ	
Forward Transconductance	g fs	V _{DS} =-15V,I _D =-4A	16	-	-	S	
Dynamic Characteristics (Note4)	····						
Input Capacitance	C _{lss}	(1 - 25)(1)(1 - 20)(1)	-	1450	-	PF	
Output Capacitance	Coss	V _{DS} =-25V,V _{GS} =0V, F=1.0MHz	-	145	-	PF	
Reverse Transfer Capacitance	C _{rss}		-	110	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	8	-	nS	
Turn-on Rise Time	tr	V_{DD} =-30V, ,R _L =30 Ω	-	9	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10V, R_{GEN} =6 Ω	-	65	-	nS	
Turn-Off Fall Time	t _f		-	30	-	nS	
Total Gate Charge	Qg	(1 - 20)(1 - 40)	-	26	-	nC	
Gate-Source Charge	Q _{gs}	V _{DS} =-30V,I _D =-4A, V _{GS} =-10V	-	4.5	-	nC	
Gate-Drain Charge	Q _{gd}	V _{GS} 10V	-	7	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-4A	-	-	-1.2	V	
Diode Forward Current (Note 2)	I _S		-	-	-4	А	

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

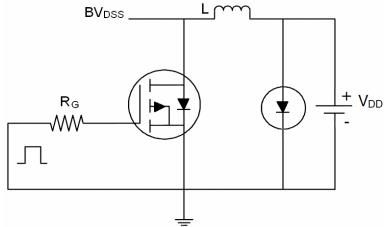
4. Guaranteed by design, not subject to production



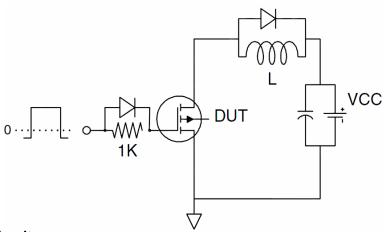




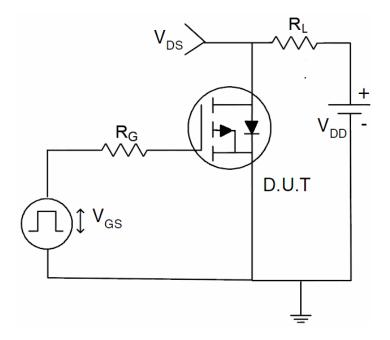
Test Circuit 1) E_{AS} Test Circuit



2) Gate Charge Test Circuit

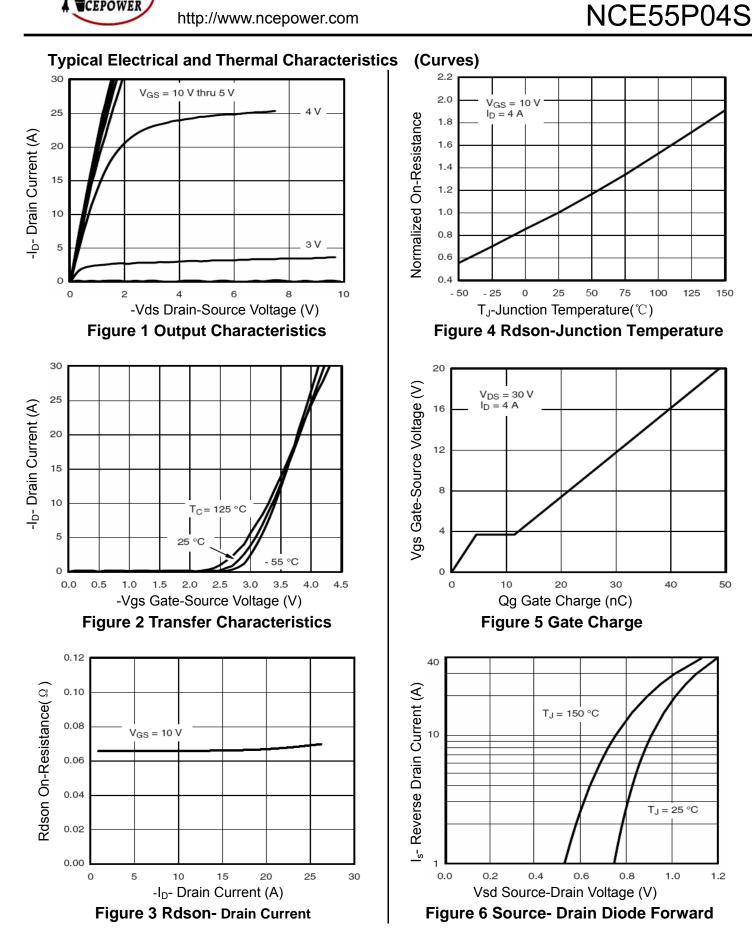


3) Switch Time Test Circuit

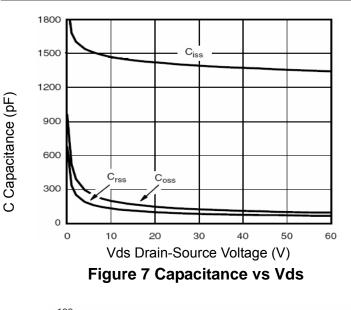












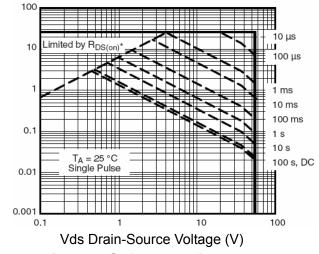
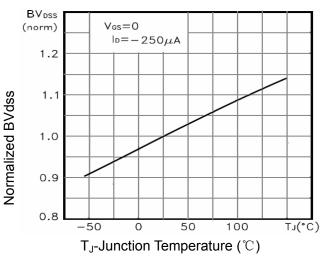


Figure 8 Safe Operation Area



Pb Free Product

NCE55P04S

Figure 9 BV_{DSS} vs Junction Temperature

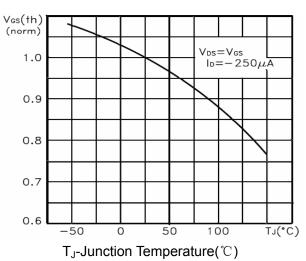
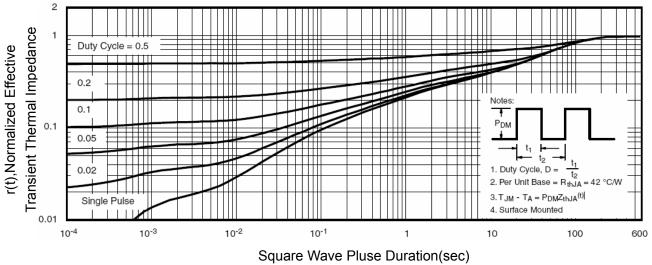


Figure 10 V_{GS(th)} vs Junction Temperature





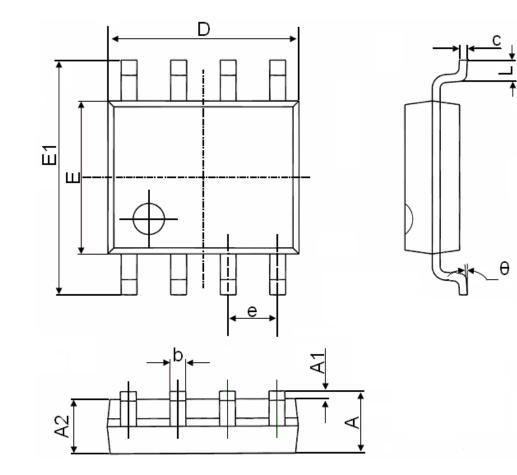
l_D- Drain Current (A)

Wuxi NCE Power Semiconductor Co., Ltd





SOP-8 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
с	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
e	1.270(BSC)		0.050(BSC)		
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	







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